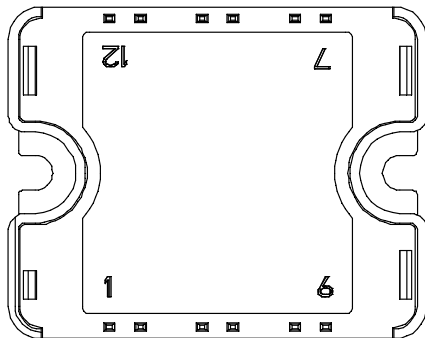
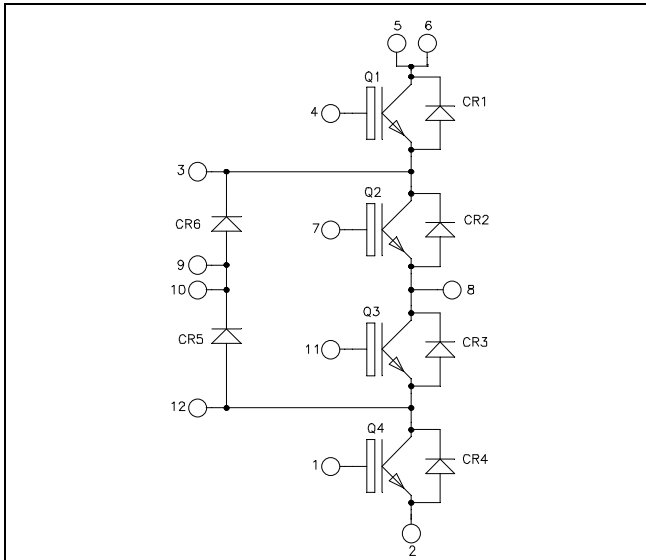


**Three level inverter  
Trench + Field Stop IGBT3  
Power Module**

**$V_{CES} = 600V$   
 $I_C = 50A @ T_c = 80^\circ C$**



All multiple inputs and outputs must be shorted together  
5/6 ; 9/10

**Application**

- Solar converter
- Uninterruptible Power Supplies

**Features**

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- High level of integration

**Benefits**

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

**Q1 to Q4 Absolute maximum ratings**

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	600	V
$I_C$	Continuous Collector Current	$T_C = 25^\circ C$	80
		$T_C = 80^\circ C$	50
$I_{CM}$	Pulsed Collector Current	$T_C = 25^\circ C$	100
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_C = 25^\circ C$	176
RBSOA	Reverse Bias Safe Operating Area	$T_J = 150^\circ C$	100A @ 550V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.  
See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Q1 to Q4 Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$			250	$\mu\text{A}$
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$		1.5	1.9	V
		$I_C = 50A$	$T_j = 25^\circ\text{C}$			
				1.7		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 600\mu\text{A}$	5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			600	nA

**Q1 to Q4 Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1\text{MHz}$		3150		pF
$C_{oes}$	Output Capacitance			200		
$C_{res}$	Reverse Transfer Capacitance			95		
$Q_G$	Gate charge	$V_{GE} = \pm 15V, I_C = 50A$ $V_{CE} = 300V$		0.5		$\mu\text{C}$
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 50A$ $R_G = 8.2\Omega$		110		ns
$T_r$	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			200		
$T_f$	Fall Time			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $150^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 50A$ $R_G = 8.2\Omega$		120		ns
$T_r$	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			250		
$T_f$	Fall Time			60		
$E_{on}$	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 50A$ $R_G = 8.2\Omega$	$T_j = 25^\circ\text{C}$	0.3		mJ
			$T_j = 150^\circ\text{C}$	0.43		
$E_{off}$	Turn-off Switching Energy	$I_C = 50A$ $R_G = 8.2\Omega$	$T_j = 25^\circ\text{C}$	1.35		mJ
			$T_j = 150^\circ\text{C}$	1.75		
$I_{sc}$	Short Circuit data	$V_{GE} \leq 15V ; V_{Bus} = 360V$ $t_p \leq 6\mu\text{s} ; T_j = 150^\circ\text{C}$		250		A
$R_{thJC}$	Junction to Case Thermal Resistance				0.85	$^\circ\text{C/W}$

**CR1 to CR4 diode ratings and characteristics**

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			600			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =600V	T <sub>j</sub> = 25°C			150	μA
			T <sub>j</sub> = 150°C			350	
I <sub>F</sub>	DC Forward Current		T <sub>c</sub> = 80°C		30		A
V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> = 30A V <sub>GE</sub> = 0V	T <sub>j</sub> = 25°C		1.6	2	V
			T <sub>j</sub> = 150°C		1.5		
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 30A V <sub>R</sub> = 300V di/dt = 1800A/μs	T <sub>j</sub> = 25°C		100		ns
			T <sub>j</sub> = 150°C		150		
Q <sub>rr</sub>	Reverse Recovery Charge		T <sub>j</sub> = 25°C		1.5		μC
			T <sub>j</sub> = 150°C		3.1		
E <sub>rr</sub>	Reverse Recovery Energy		T <sub>j</sub> = 25°C		0.34		mJ
			T <sub>j</sub> = 150°C		0.75		
R <sub>thJC</sub>	Junction to Case Thermal Resistance					2.45	°C/W

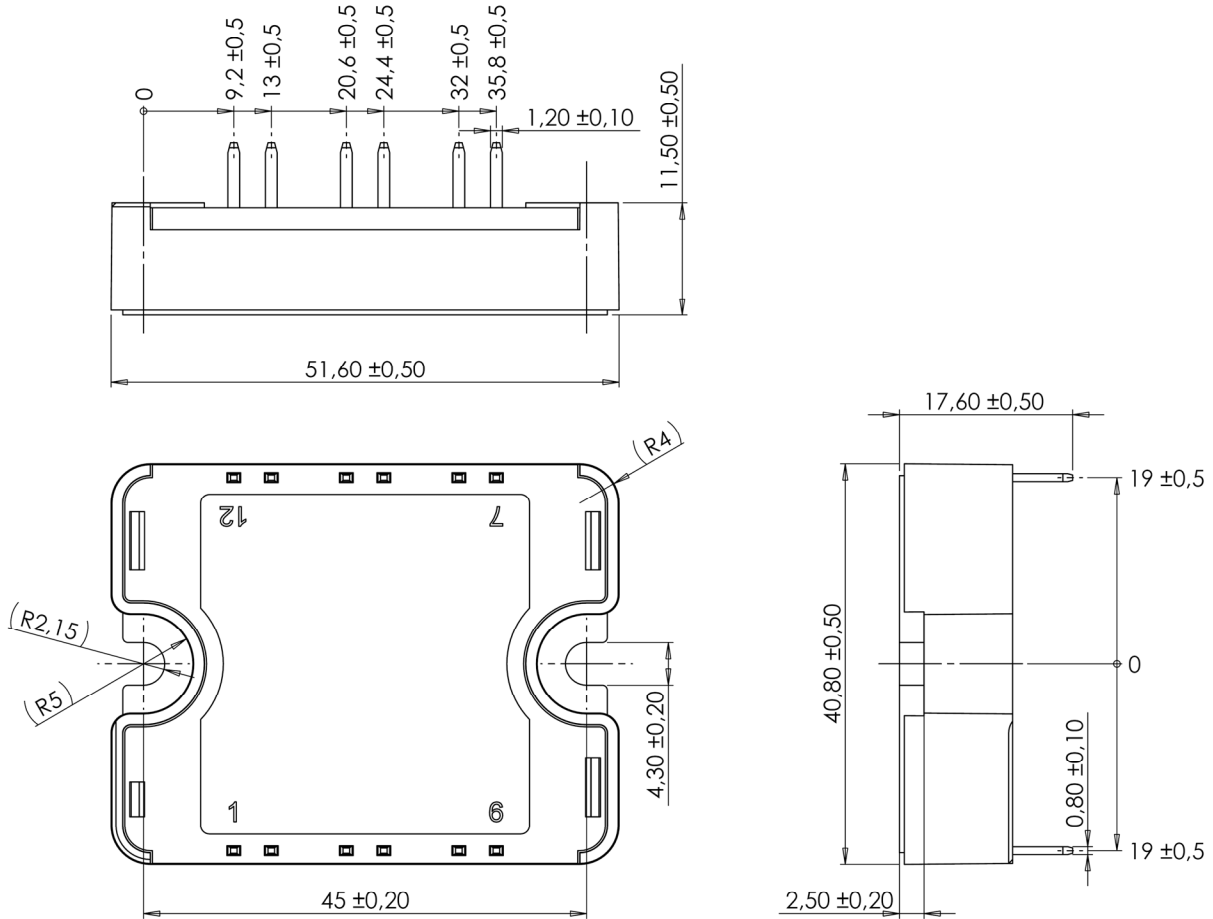
**CR5 & CR6 diode ratings and characteristics**

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			600			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =600V	T <sub>j</sub> = 25°C			150	μA
			T <sub>j</sub> = 150°C			350	
I <sub>F</sub>	DC Forward current		T <sub>c</sub> = 80°C		50		A
V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> = 50A V <sub>GE</sub> = 0V	T <sub>j</sub> = 25°C		1.6	2	V
			T <sub>j</sub> = 150°C		1.5		
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 50A V <sub>R</sub> = 300V di/dt = 1800A/μs	T <sub>j</sub> = 25°C		100		ns
			T <sub>j</sub> = 150°C		150		
Q <sub>rr</sub>	Reverse Recovery Charge		T <sub>j</sub> = 25°C		2.6		μC
			T <sub>j</sub> = 150°C		5.4		
E <sub>rr</sub>	Reverse Recovery Energy		T <sub>j</sub> = 25°C		0.60		mJ
			T <sub>j</sub> = 150°C		1.20		
R <sub>thJC</sub>	Junction to Case Thermal Resistance					1.42	°C/W

**Thermal and package characteristics**

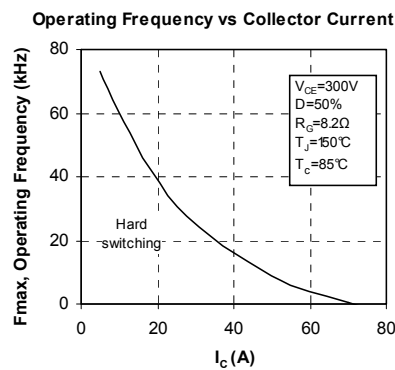
<i>Symbol</i>	<i>Characteristic</i>			<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
T <sub>J</sub>	Operating junction temperature range			-40		175	°C
T <sub>STG</sub>	Storage Temperature Range			-40		125	
T <sub>C</sub>	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					80	g

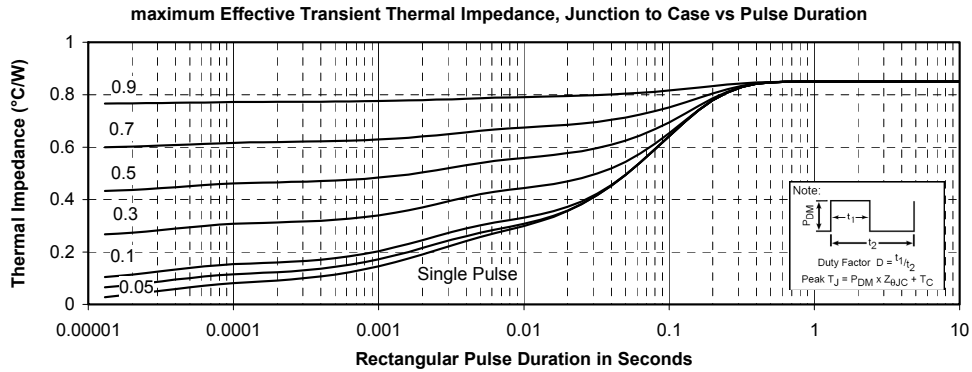
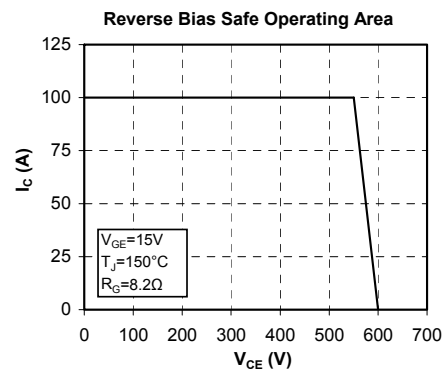
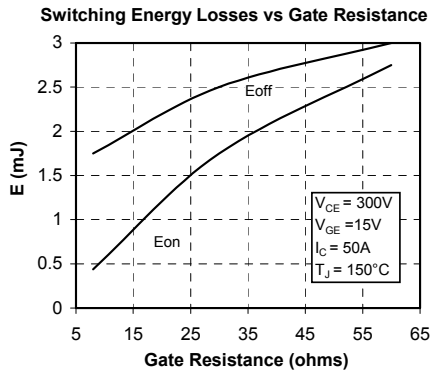
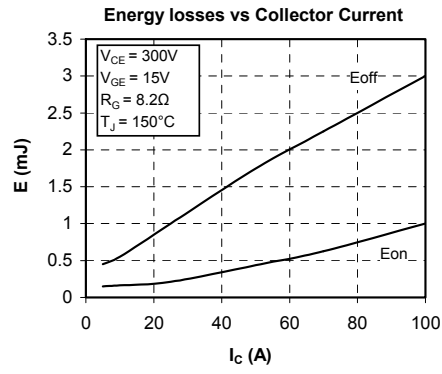
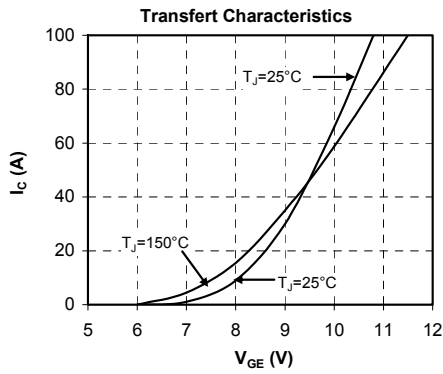
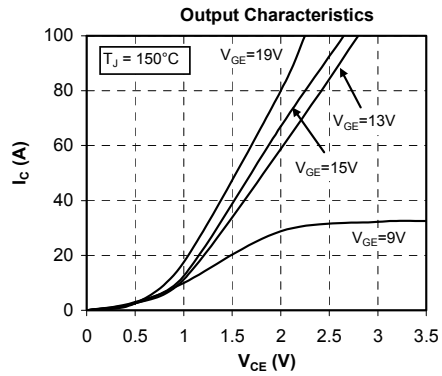
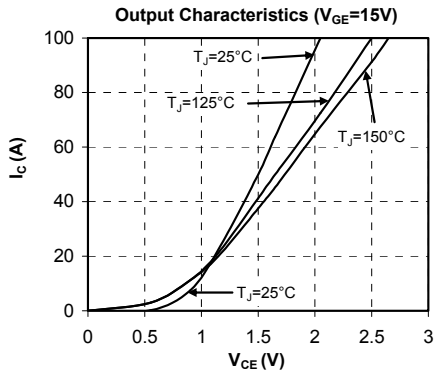
**SP1 Package outline** (dimensions in mm)

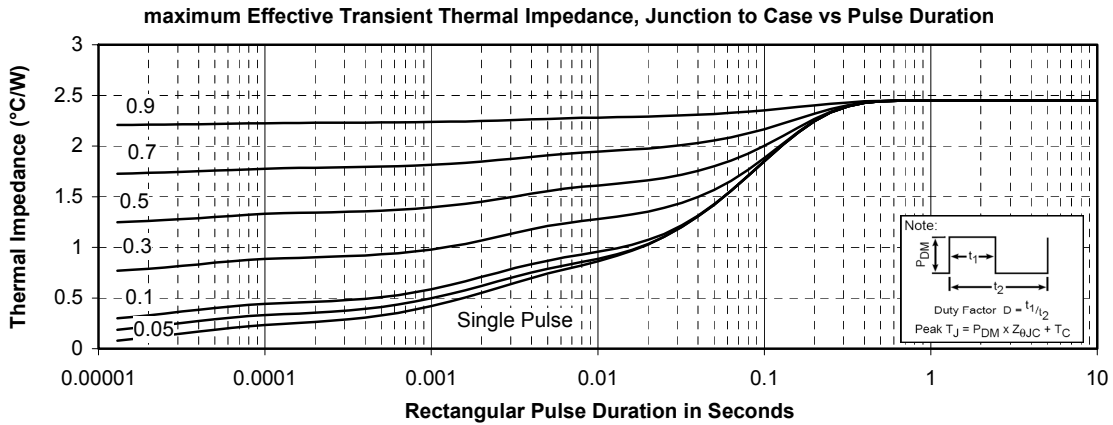
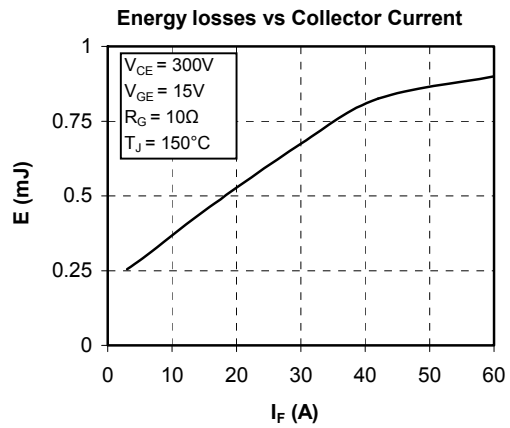
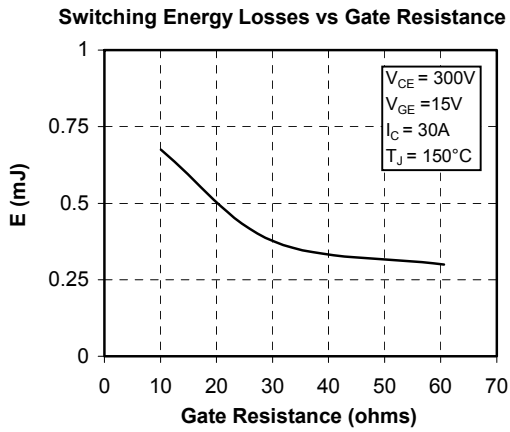
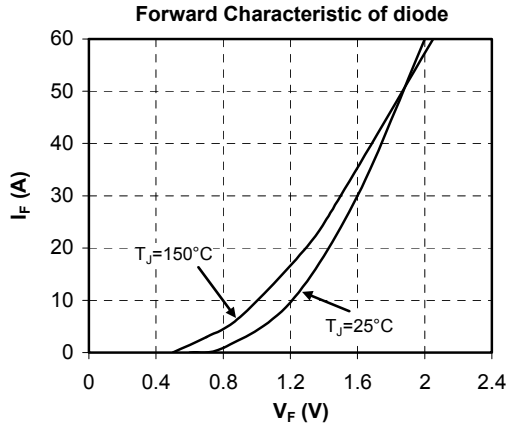


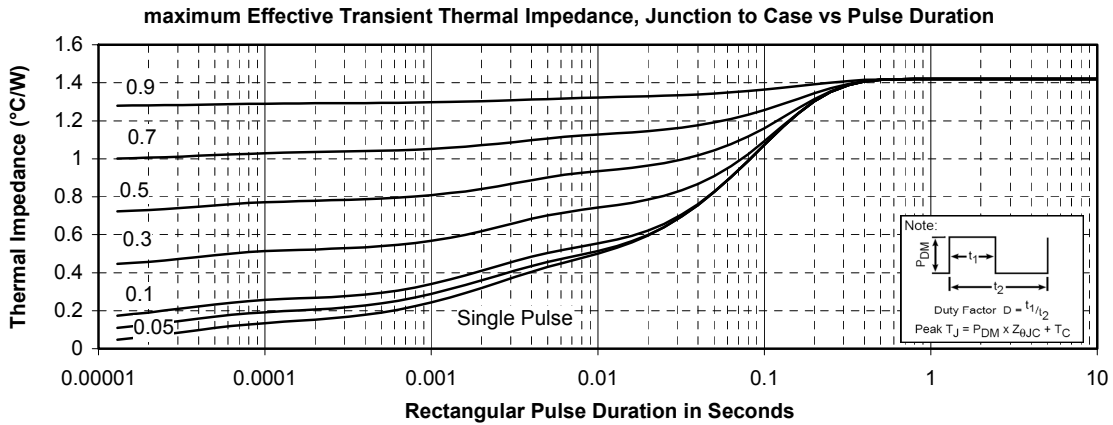
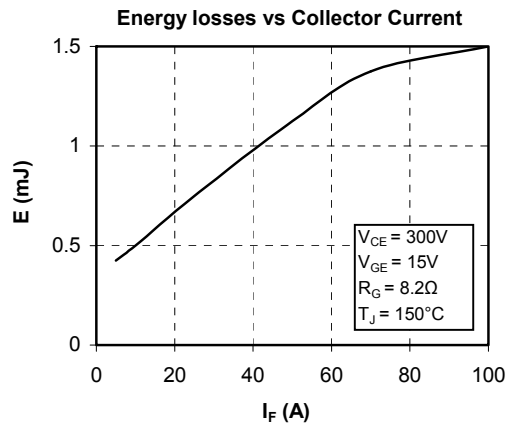
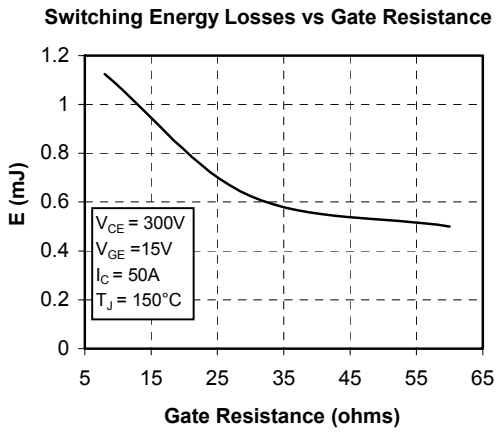
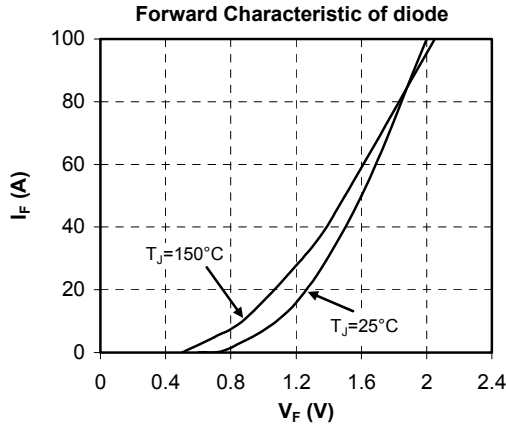
See application note 1904 - Mounting Instructions for SP1 Power Modules on [www.microsemi.com](http://www.microsemi.com)

**Q1 to Q4 Typical performance curve**





**CR1 to CR4 Typical performance curve**


**CR5 & CR6 Typical performance curve**


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